

# **Standard Rectifier Module**

= 2x 1800 V

300 A

 $V_{\mathsf{F}}$ 1 V

## Phase leg

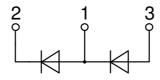
#### Part number

#### MDD310-18N1



Backside: isolated





#### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

#### **Applications:**

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

#### Package: Y2

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- · Reduced weight
- Advanced power cycling

#### Terms \_Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

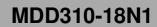
Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

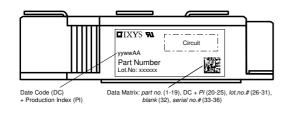




Rectifier			Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse bloc	cking voltage	$T_{VJ} = 25^{\circ}C$			1900	٧
V <sub>RRM</sub>	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1800	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1800 V	$T_{VJ} = 25^{\circ}C$			1	mA
		$V_R = 1800 \text{ V}$	$T_{VJ} = 150$ °C			20	mΑ
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 300 A	$T_{VJ} = 25^{\circ}C$			1.13	V
		$I_F = 600 A$				1.33	٧
		$I_F = 300 \text{ A}$	T <sub>VJ</sub> = 125°C			1.00	٧
		$I_F = 600 A$				1.29	٧
I FAV	average forward current	T <sub>C</sub> = 100°C	T <sub>vJ</sub> = 150°C			300	Α
I F(RMS)	RMS forward current	180° sine				480	Α
V <sub>F0</sub>	threshold voltage		T <sub>vJ</sub> = 150°C			0.75	٧
r <sub>F</sub>	slope resistance } for power	loss calculation only				0.63	mΩ
R <sub>thJC</sub>	thermal resistance junction to ca	ase				0.13	K/W
R <sub>thCH</sub>	thermal resistance case to heats	sink			0.04		K/W
P <sub>tot</sub>	total power dissipation		$T_{C} = 25^{\circ}C$			960	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			11.5	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			12.4	kA
		t = 10 ms; (50 Hz), sine	T <sub>vJ</sub> = 150°C			9.78	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			10.6	kA
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			661.3	kA2s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			641.7	kA2s
		t = 10 ms; (50 Hz), sine	T <sub>vJ</sub> = 150°C			477.8	kA2s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			463.5	kA2s
C	junction capacitance	$V_R = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		381		pF



Package Y2			Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal				600	Α
T <sub>VJ</sub>	virtual junction temperature			-40		150	°C
T <sub>op</sub>	operation temperature			-40		125	°C
T <sub>stg</sub>	storage temperature			-40		125	°C
Weight					254		g
M <sub>D</sub>	mounting torque			2.5		5	Nm
$\mathbf{M}_{\scriptscriptstyleT}$	terminal torque			12		15	Nm
d <sub>Spp/App</sub>	creepage distance on surface   striking distance through a	riking diatanaa through air	terminal to terminal	13.0			mm
d <sub>Spb/Apb</sub>	creepage distance on surface   St	terminal to backside		13.0			mm
V <sub>ISOL</sub>	isolation voltage	t = 1 second		3600			٧
1002	t = 1	t = 1 minute	50/60 Hz, RMS; IISOL ≤ 1 mA	3000			٧

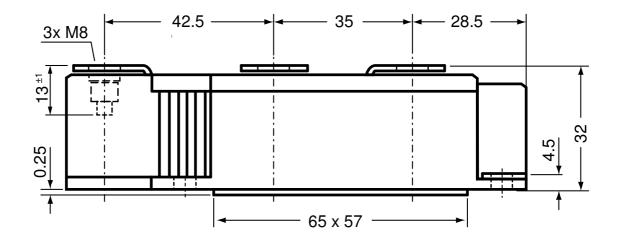


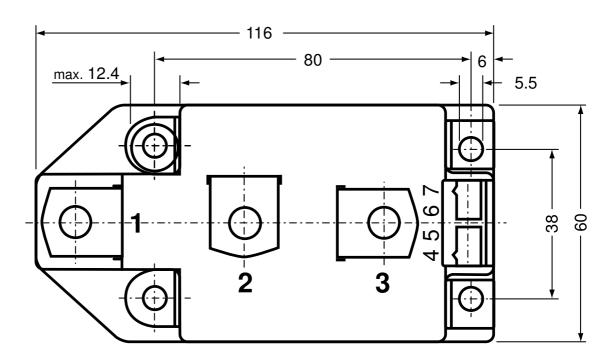
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD310-18N1	MDD310-18N1	Box	2	463973

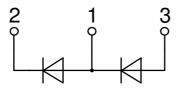
Equiva	alent Circuits for	Simulation	* on die level	T <sub>vJ</sub> = 150 °C
$I \rightarrow V_0$	$R_0$	Rectifier		
V <sub>0 max</sub>	threshold voltage	0.75		V
$R_{0 \text{ max}}$	slope resistance *	0.34		mΩ



## Outlines Y2

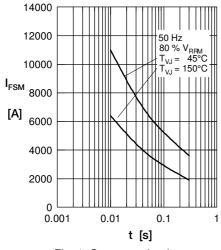


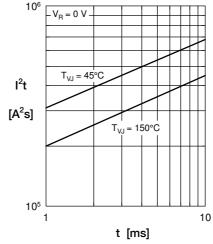






### Rectifier





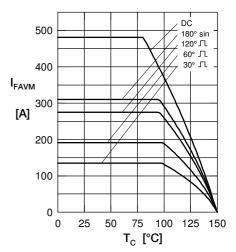


Fig. 1 Surge overload current I<sub>FSM</sub>: Crest value, t: duration

Fig. 2 I<sup>2</sup>t versus time (1-10 ms)

Fig. 3 Maximum forward current at case temperature

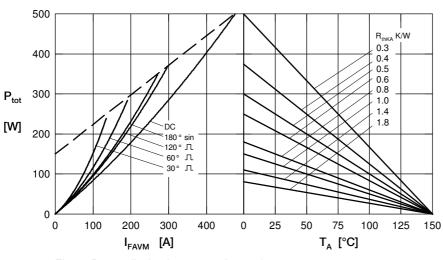


Fig. 4 Power dissipation versus forward current and ambient temperature (per diode)

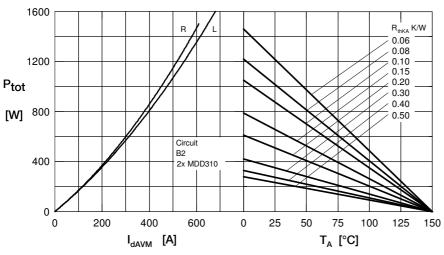


Fig. 5 Single phase rectifier bridge: Power dissipation vs. direct output current and ambient temperature R = resistive load, L = inductive load



#### Rectifier

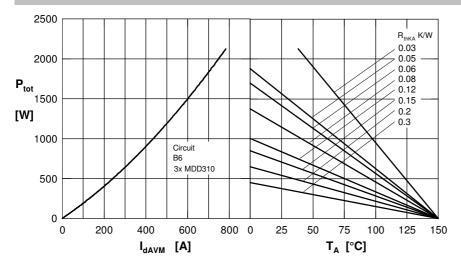


Fig.6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

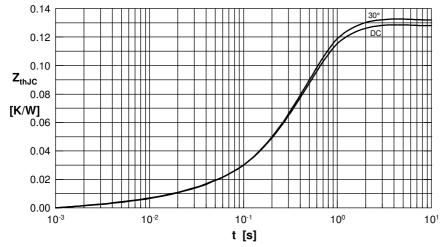


Fig. 7 Transient thermal impedance junction to case (per diode)

R<sub>th.IC</sub> for various conduction angles d

liloC	
d	R <sub>thJC</sub> [K/W]
DC	0.129
180°	0.131
120°	0.132
60°	0.132
30°	0.133

Constants for  $Z_{thJC}$  calculation:

i	R <sub>thi</sub> [K/W]	t <sub>i</sub> [s]
1	0.0035	0.0099
2	0.0165	0.1680
3	0.1091	0.4560

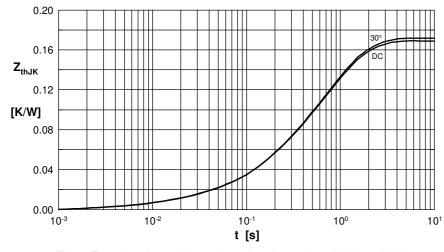


Fig. 8 Transient thermal impedance junction to heatsink (per diode)

 $\boldsymbol{R}_{\text{thJK}}$  for various conduction angles d

tnjk	
d	$R_{thJK}$ [K/W]
DC	0.169
180°	0.171
120°	0.172
60°	0.172
30°	0.173

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ (K/W)	t <sub>i</sub> (s)
1	0.0035	0.0099
2	0.0165	0.1680
3	0.1091	0.4560
4	0.0400	1.3600

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